

M74HCT640

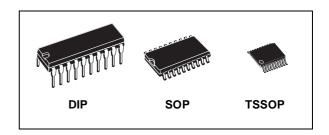
OCTAL BUS TRANSCEIVER WITH 3 STATE OUTPUTS (INVERTED)

- HIGH SPEED:
 - t_{PD} = 13ns (TYP.) at V_{CC} = 4.5V
- LOW POWER DISSIPATION: $I_{CC} = 4\mu A(MAX.)$ at $T_A=25^{\circ}C$
- COMPATIBLE WITH TTL OUTPUTS : $V_{IH} = 2V \text{ (MIN.) } V_{IL} = 0.8V \text{ (MAX)}$
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 6mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 640



The M74HCT640 is an advanced high-speed CMOS OCTAL BUS TRANSCEIVER (3-STATE) fabricated with silicon gate C²MOS technology.

This IC is intended for two-way asynchronous communication between data buses, and the direction of data transmission is determined by DIR input. The enable input \overline{G} can be used to disable the device so that the buses are effectively isolated.



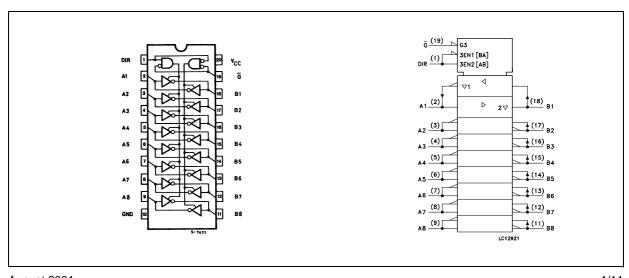
ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HCT640B1R	
SOP	M74HCT640M1R	M74HCT640RM13TR
TSSOP		M74HCT640TTR

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

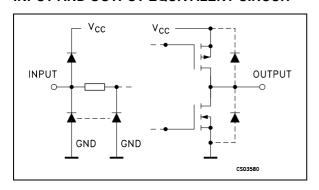
All floating bus terminals during High Z State must be held HIGH or LOW.

PIN CONNECTION AND IEC LOGIC SYMBOLS



August 2001 1/11

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

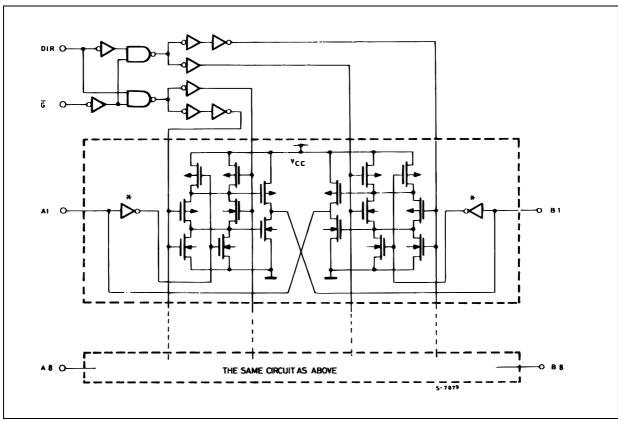
PIN No	SYMBOL	NAME AND FUNCTION
1	DIR	Directional Control
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs/Outputs
18, 17, 16, 15, 14, 13, 12, 11	B1 to B8	Data Inputs/Outputs
19	G	Output Enable Input
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

TRUTH TABLE

INP	UTS	FUNC	OUTPUT	
G	DIR	A BUS	A BUS B BUS	
L	L	OUTPUT	INPUT	$A = \overline{B}$
L	Н	INPUT	OUTPUT	$B = \overline{A}$
Н	X	Z	Z	Z

X : Don't Care Z : High Impedance

LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Ιο	DC Output Current	± 35	mA
I_{CC} or I_{GND}	DC V _{CC} or Ground Current	± 70	mA
P_{D}	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.5 to 5.5	V
VI	Input Voltage	0 to V _{CC}	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
t _r , t _f	Input Rise and Fall Time (V _{CC} = 4.5 to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

		7	Test Condition	Value								
Symbol	Parameter	v _{cc}		Т	A = 25°	C	-40 to	85°C	-55 to	125°C	Unit	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
V _{IH}	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V	
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	٧	
V _{OH}	High Level Output	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		V	
	Voltage	4.5	I _O =-6.0 mA	4.18 4.	4.31		4.13		4.10		V	
V _{OL}	V _{OL} Low Level Output		4.5	I _O =20 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I _O =6.0 mA		0.17	0.26		0.33		0.40	v	
I _I	Input Leakage Current	5.5	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ	
I _{OZ}	High Impedance Output Leakage Current	5.5	$V_I = V_{IH} \text{ or } V_{IL}$ $V_O = V_{CC} \text{ or GND}$			± 0.5		± 5		± 10	μΑ	
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			4		40		80	μΑ	
ΔI _{CC}	Additional Worst Case Supply Current	5.5	Per Input pin $V_{I} = 0.5V \text{ or}$ $V_{I} = 2.4V$ Other Inputs at $V_{CC} \text{ or GND}$ $I_{O} = 0$			2.0		2.9		3.0	mA	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

		Test Condition			Value							
Symbol Parameter	Parameter	ν _{cc}			Т	T _A = 25°C		-40 to 85°C		-55 to 125°C		Unit
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	4.5	50			7	12		15		18	ns
t _{PLH} t _{PHL}	Propagation Delay	4.5	50			13	22		28		33	nc
	Time	4.5	150			18	30		38		45	ns
t _{PZL} t _{PZH}	High Impedance	4.5	50	$R_L = 1 K\Omega$		19	30		38		45	
	Output Enable Time	4.5	150	$R_L = 1 \text{ K}\Omega$		24	38		48		57	ns
t _{PLZ} t _{PHZ}	High Impedance Output Disable Time	4.5	50	R _L = 1 KΩ		17	30		38		45	ns

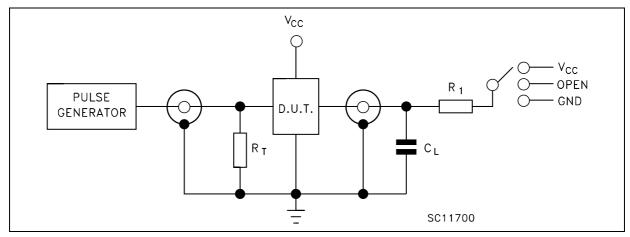
CAPACITIVE CHARACTERISTICS

		Test Condition		Value								
Symbol	Parameter	ν _{cc}			T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
			(v)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance			DIR, G		5	10		10		10	pF
C _{I/OUT}	Output Capacitance			An, Bn		13						pF
C _{PD}	Power Dissipation Capacitance (note 1)					37						pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per circuit)

577

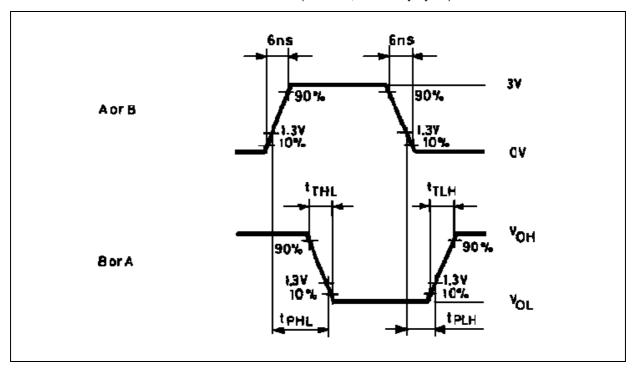
TEST CIRCUIT



TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	V _{CC}
t _{PZH} , t _{PHZ}	GND

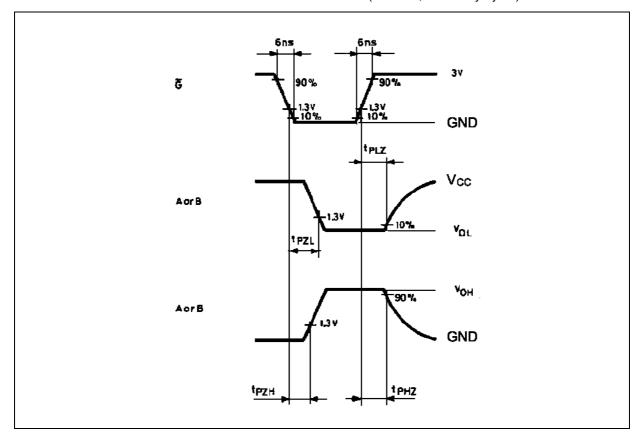
 $C_L = 50 pF/150 pF$ or equivalent (includes jig and probe capacitance) $R_1 = 1 K \Omega$ or equivalent $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



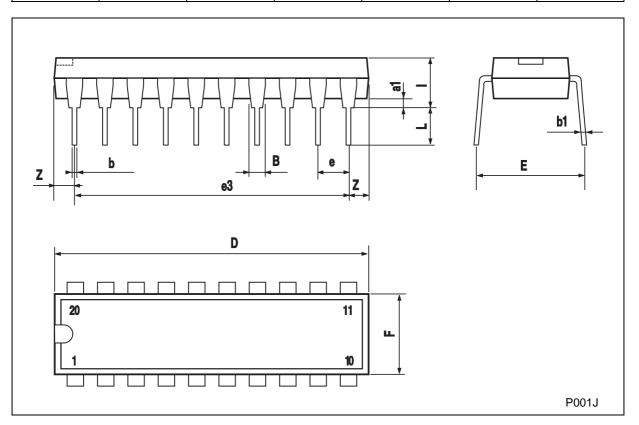
47/ 6/11

WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)



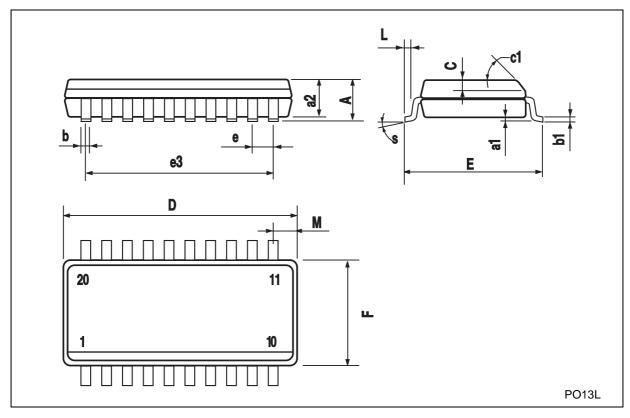
Plastic DIP-20 (0.25) MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
a1	0.254			0.010			
В	1.39		1.65	0.055		0.065	
b		0.45			0.018		
b1		0.25			0.010		
D			25.4			1.000	
E		8.5			0.335		
е		2.54			0.100		
e3		22.86			0.900		
F			7.1			0.280	
I			3.93			0.155	
L		3.3			0.130		
Z			1.34			0.053	



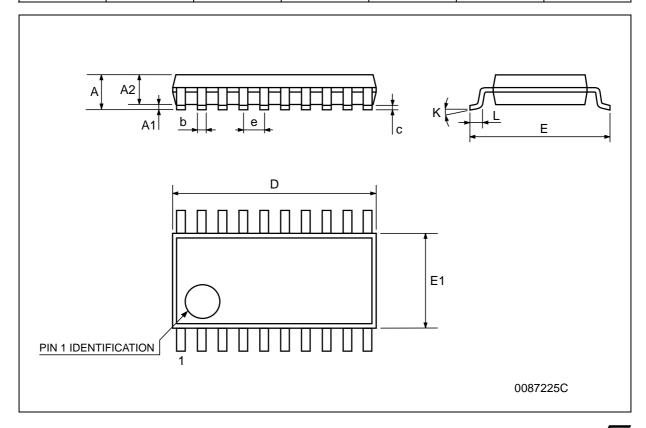
SO-20 MECHANICAL DATA

DIM		mm.		inch					
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
Α			2.65			0.104			
a1	0.1		0.2	0.004		0.008			
a2			2.45			0.096			
b	0.35		0.49	0.014		0.019			
b1	0.23		0.32	0.009		0.012			
С		0.5			0.020				
c1			45°	(typ.)					
D	12.60		13.00	0.496		0.512			
Е	10.00		10.65	0.393		0.419			
е		1.27			0.050				
e3		11.43			0.450				
F	7.40		7.60	0.291		0.300			
L	0.50		1.27	0.020		0.050			
М			0.75			0.029			
S		ı	8° (r	max.)					



TSSOP20 MECHANICAL DATA

DIM.		mm.		inch			
DIN.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			1.2			0.047	
A1	0.05		0.15	0.002	0.004	0.006	
A2	0.8	1	1.05	0.031	0.039	0.041	
b	0.19		0.30	0.007		0.012	
С	0.09		0.20	0.004		0.0089	
D	6.4	6.5	6.6	0.252	0.256	0.260	
E	6.2	6.4	6.6	0.244	0.252	0.260	
E1	4.3	4.4	4.48	0.169	0.173	0.176	
е		0.65 BSC			0.0256 BSC		
К	0°		8°	0°		8°	
L	0.45	0.60	0.75	0.018	0.024	0.030	



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco Singapore - Spain - Sweden - Switzerland - United Kingdom © http://www.st.com

